

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
100V	122mΩ @ V <sub>GS</sub> = 10V	2.9A
	133mΩ @ V <sub>GS</sub> = 4.5V	2.7A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

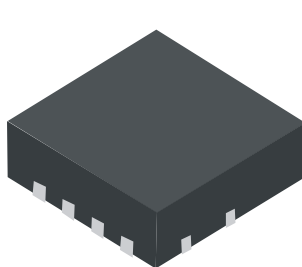
## Features

- 100% Unclamped Inductive Switching, Test in Production – Ensures more reliable and robust end application
- Low R<sub>DS(ON)</sub> – Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

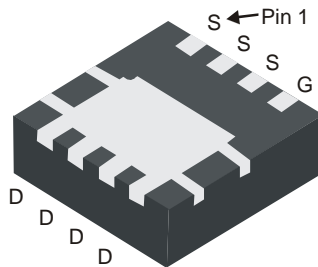
## Mechanical Data

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.03 grams (Approximate)

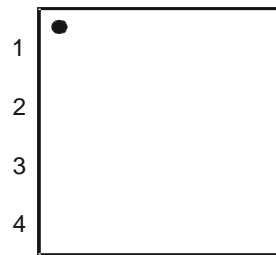
PowerDI3333-8



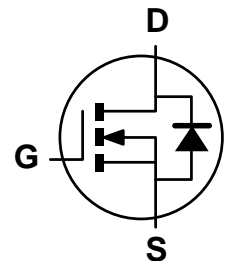
Top View



Bottom View



Top View



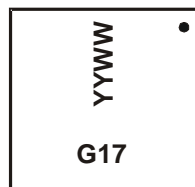
Equivalent Circuit

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMN10H170SFGQ-7	PowerDI3333-8	2000/Tape & Reel
DMN10H170SFGQ-13	PowerDI3333-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



G17 = Product Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 19 for 2019)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	I <sub>D</sub>	T <sub>A</sub> = +25°C	2.9
			T <sub>A</sub> = +70°C	2.4
	T <sub>C</sub> = +25°C		8.5	
	t < 10s	I <sub>D</sub>	T <sub>A</sub> = +25°C	3.7
			T <sub>A</sub> = +70°C	3.0
Maximum Continuous Body Diode Forward Current (Note 7)		I <sub>S</sub>	3.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	16	A
Avalanche Current (Note 8)		I <sub>AS</sub>	5.3	A
Avalanche Energy (Note 8)		E <sub>AS</sub>	20	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.94	W
	T <sub>A</sub> = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	137	°C/W
	t < 10s		82	
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.0	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>θJA</sub>	60	°C/W
	t < 10s		36	
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	7.0	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	µA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	99	122	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.3A
		—	104	133		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	4.4	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.3A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.3A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	870.7	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	40.8	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	24.6	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	7.0	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 3.3A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	14.9	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	3.3	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.0	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.4	—	ns	V <sub>DD</sub> = 50V, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 6.0Ω, I <sub>D</sub> = 3.3A
Turn-On Rise Time	t <sub>R</sub>	—	2.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	13.9	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	3.4	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	22.4	—	ns	I <sub>S</sub> = 3.3A, dI/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	19.7	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - UIS in production with L = 1.43mH, T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

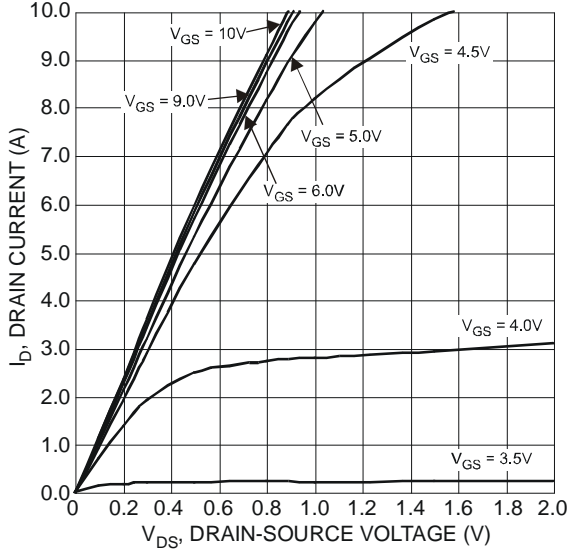


Figure 1 Typical Output Characteristic

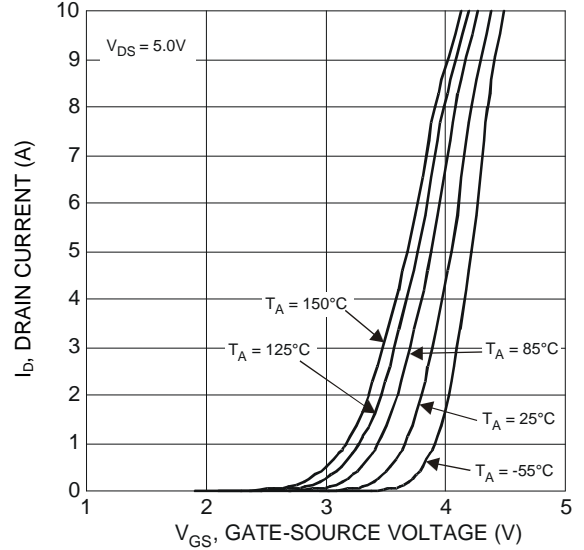


Figure 2 Typical Transfer Characteristics

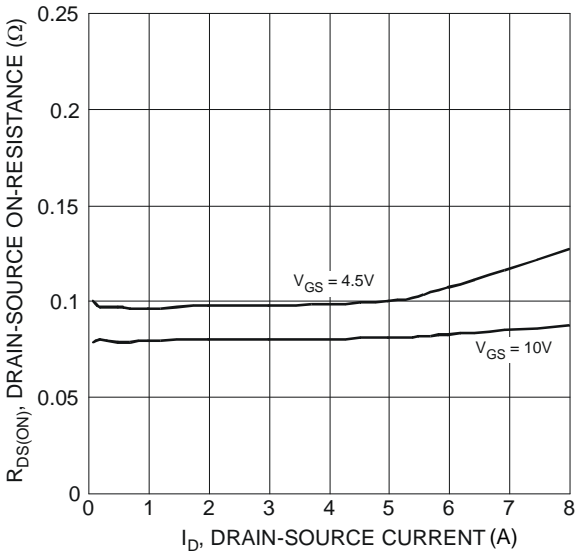


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

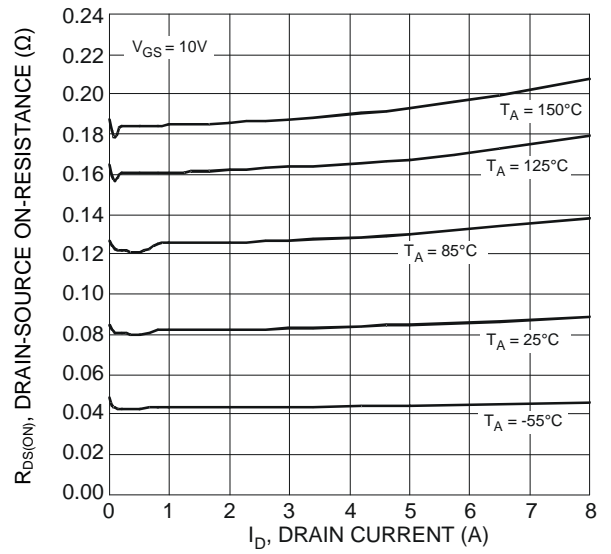


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

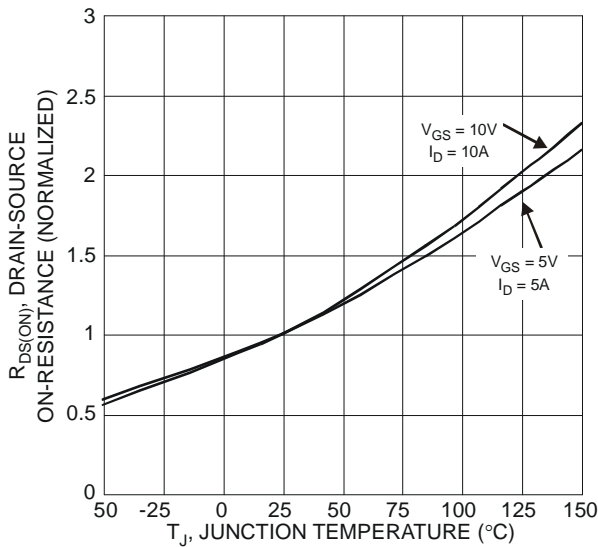


Figure 5 On-Resistance Variation with Temperature

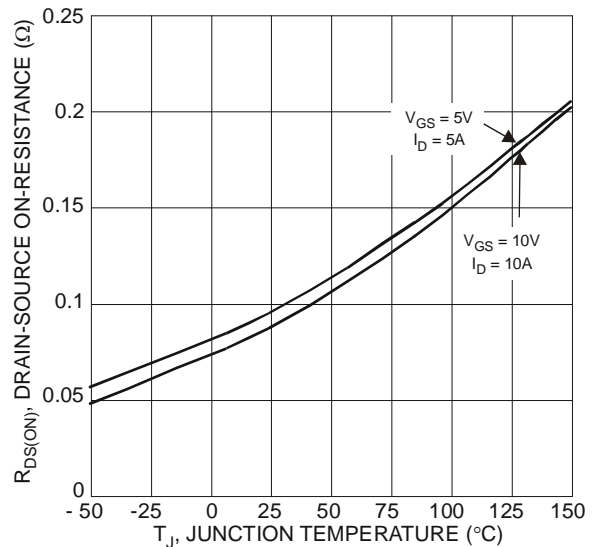


Figure 6 On-Resistance Variation with Temperature

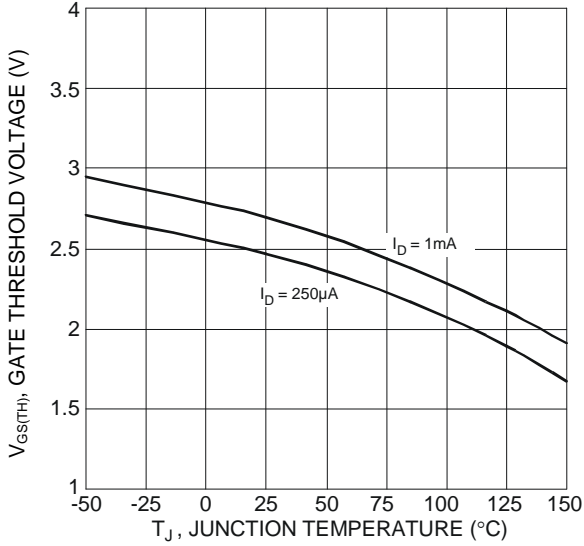


Figure 7 Gate Threshold Variation vs. Junction Temperature

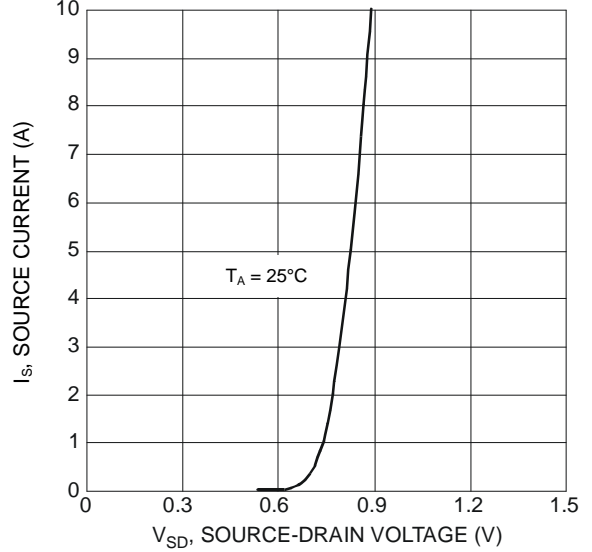


Figure 8 Diode Forward Voltage vs. Current

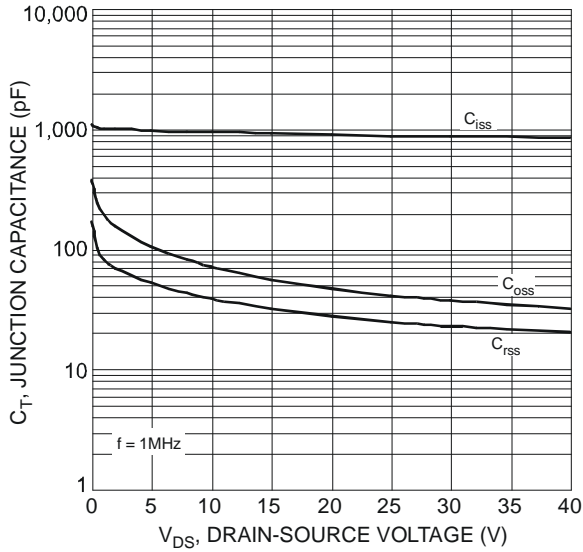


Figure 9 Typical Junction Capacitance

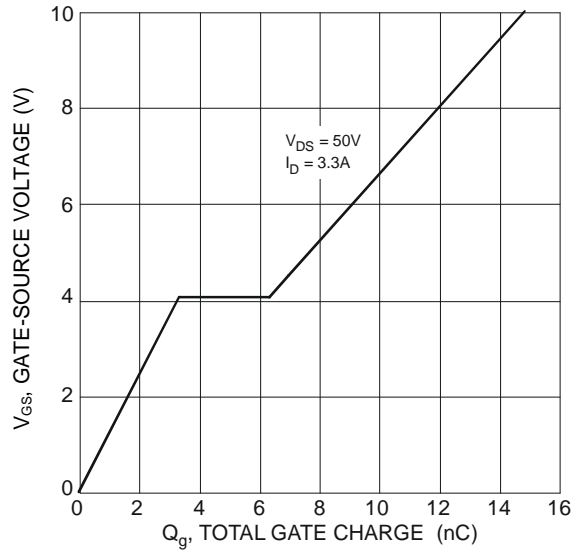


Figure 10 Gate Charge

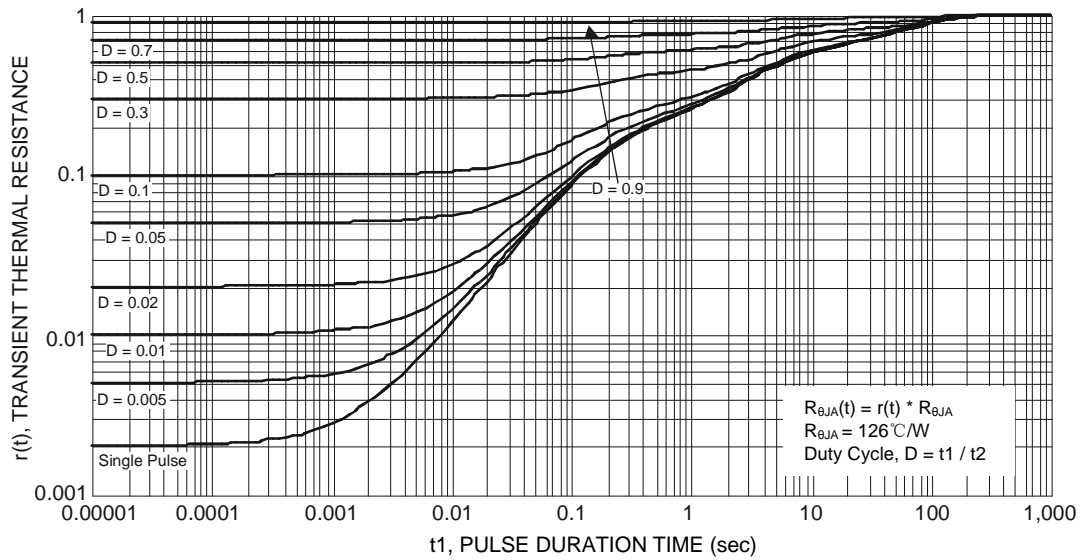
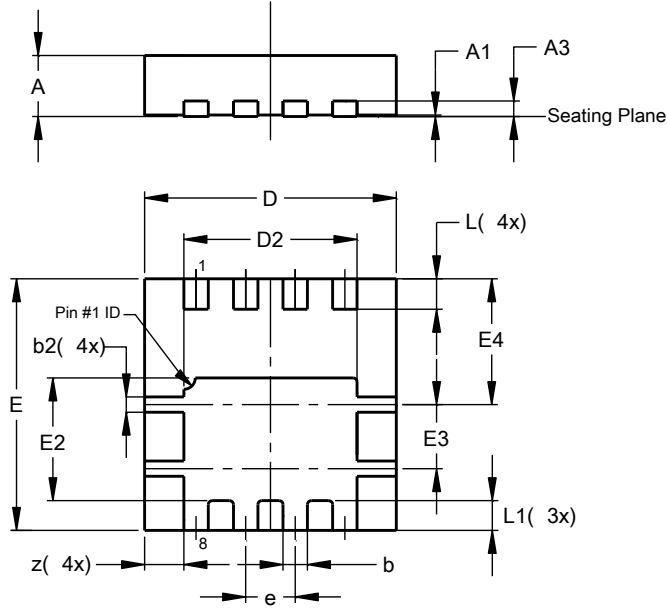


Figure 11 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

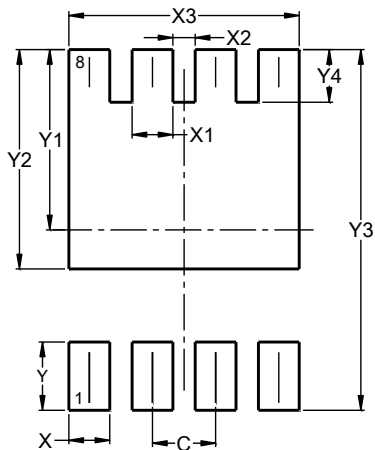


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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